

# A mechanism of inhibition of phase transitions in nano-grained close-packed Pd thin films

E. Hüger<sup>1</sup>, T. Káňa<sup>2,3</sup>, M. Šob<sup>4,2</sup>

<sup>1</sup>*Institute of Metallurgy, Clausthal University of Technology, Clausthal-Zellerfeld, Gero cp{*

<sup>2</sup>*Institute of Physics of Materials, Academy of Sciences of the Czech Republic*

<sup>3</sup>*Faculty of Mechanical Engineering, Brno University of Technology, Czech Republic*

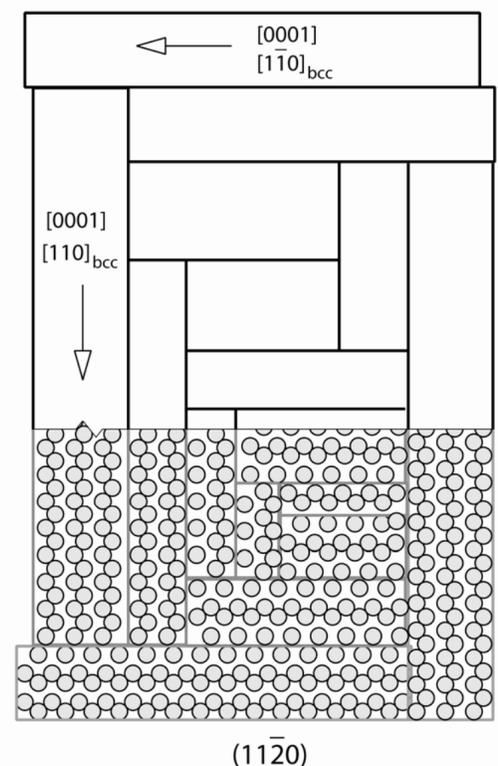
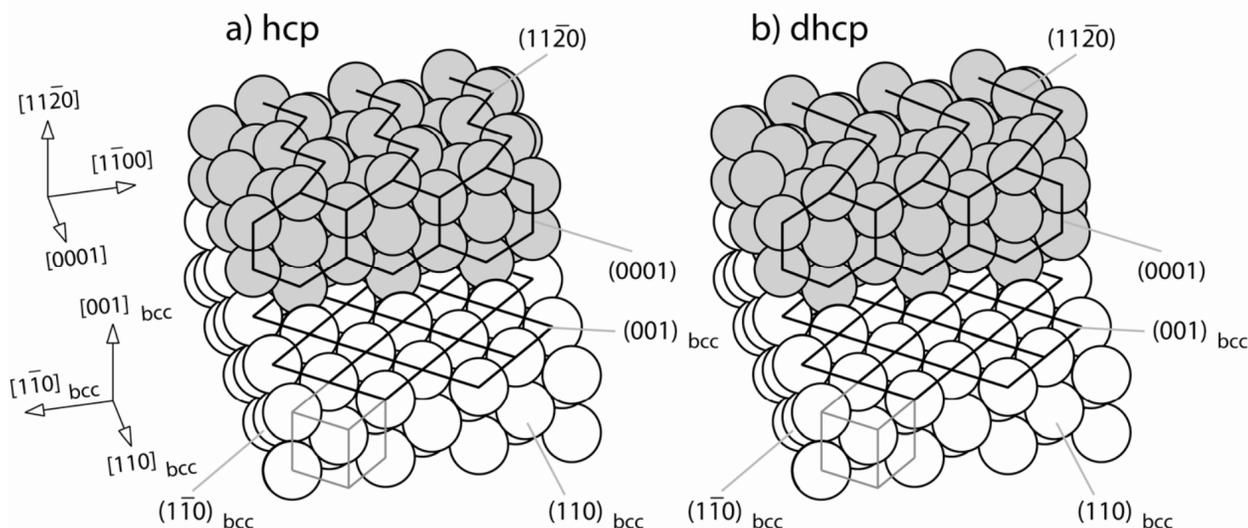
<sup>4</sup>*Department of Chemistry, Faculty of Science, Masaryk University, Czech Republic*

## Motivation

Mechanical behavior of materials can be tailored by introducing microstructural obstacles (such as grain boundaries) to dislocation motion [1]. In some cases, such obstacles may even inhibit a phase transformation from a higher-energy configuration back into the ground-state phase [2-4]. Here we explain how a grain boundary network can block the change of the crystal structure inside Pd nanograins [4]. In nanocrystalline materials, both higher-temperature phases at low temperature and lower-temperature phases at high-temperature have been observed. The obstacles (of any kind) may increase the energy barrier inhibiting the transformation.

## Pd nanograins on W(001)

First stage of their growth is pseudomorphic with the bcc W substrate. Then hcp islands of Pd appear. They further grow in the form of an orthogonal set of rectangular domains. After annealing the Pd film at 400 K the initial hcp structure changes to dhcp [5]. The hcp and dhcp structures are higher-energy phases, while the fcc structure is ground-state structure of Pd



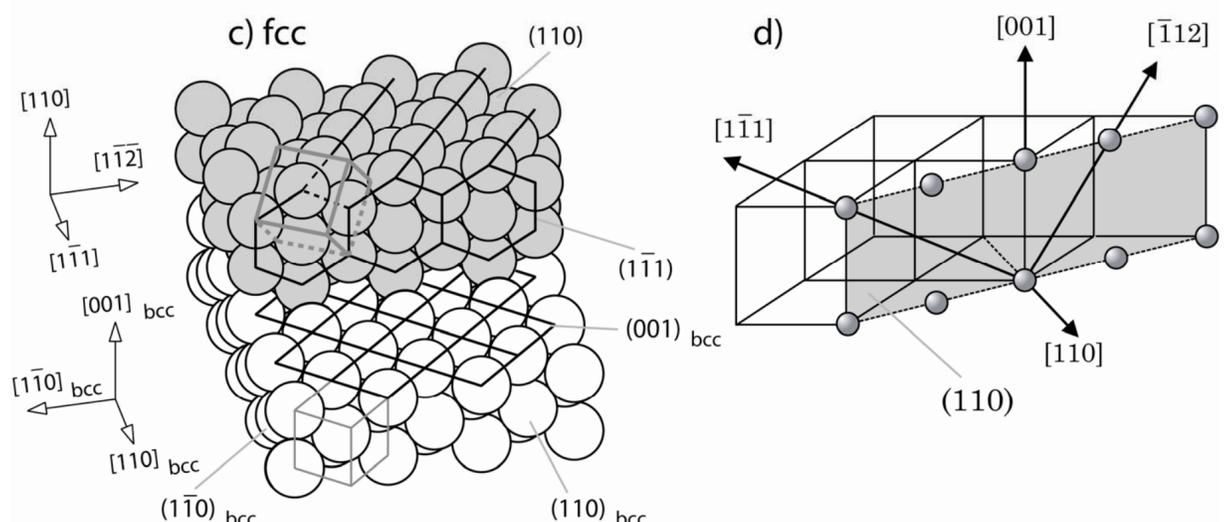
## Epitaxial relationship of Pd films on W(001) cubic substrate:

hcp  $(11\bar{2}0) \parallel \text{bcc}(001)$  and hcp $[0001] \parallel \text{bcc}\langle 110 \rangle$  (top)

The Pd close-packed planes lie perpendicular to the substrate

The *expected* epitaxial relationship of ground-state fcc Pd film on W(001) cubic substrate is  $\text{fcc}(110) \parallel \text{bcc}(001)$  and  $\text{fcc}\langle 111 \rangle \parallel \text{bcc}\langle 110 \rangle$ . (right).

This configuration is, however, not experimentally observed in Pd thin films on cubic substrates. Why?



The epitaxial misfit can control the Pd structure during growth

## Computational methods

We have used the full-potential Linearized Augmented Plane Waves (FLAPW) method implemented in the WIEN2k code. For exchange-correlation energy, both local density approximation (LDA) and generalized gradient approximation (GGA) were used. They both yield similar results for Pd structures.

### Proposed transformation paths:

hcp  $\rightarrow$  dhcp (path 4)

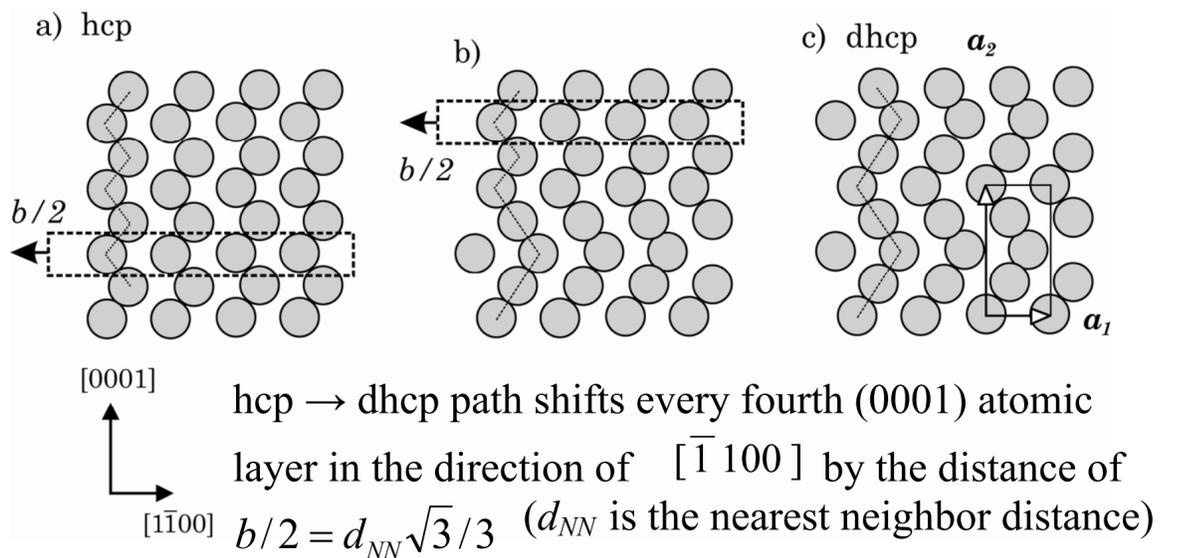
hcp  $\rightarrow$  fcc (paths 1-3)

The paths are described using bulk primitive unit cell. This cell is deformed (hcp  $\rightarrow$  fcc paths 1-2) or remains fixed in space (hcp  $\rightarrow$  fcc path 3, hcp  $\rightarrow$  dhcp path)

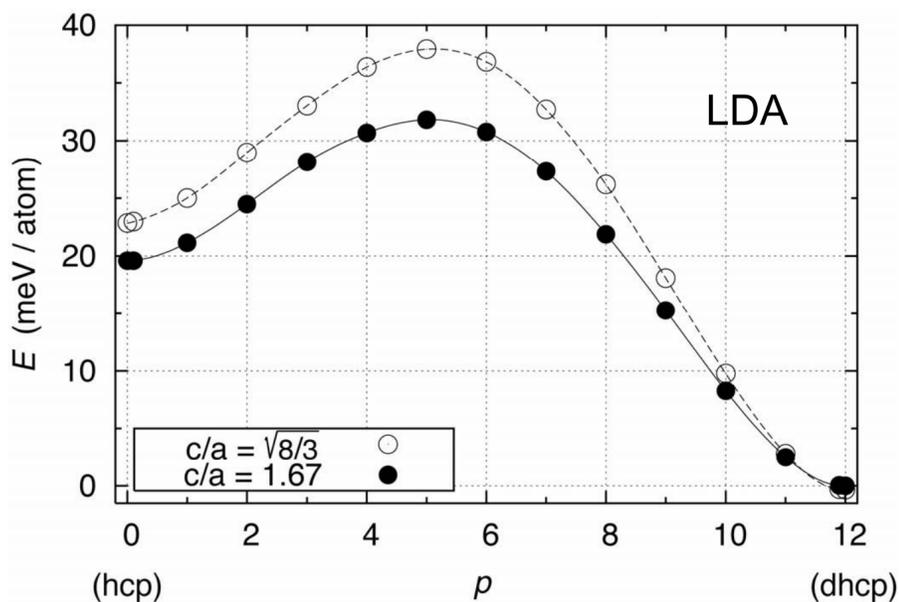
### Transformation path hcp $\rightarrow$ dhcp

Figs. (a) - (c) show  $(11\bar{2}0)$  atomic planes of the Pd adsorbate.

The (bulk) unit cell is shown in Fig. (c) - vectors  $\mathbf{a}_1, \mathbf{a}_2$ , (vector  $\mathbf{a}_3$  is perpendicular to the plane of the figure)



### Total-energy profile of the hcp $\rightarrow$ dhcp path

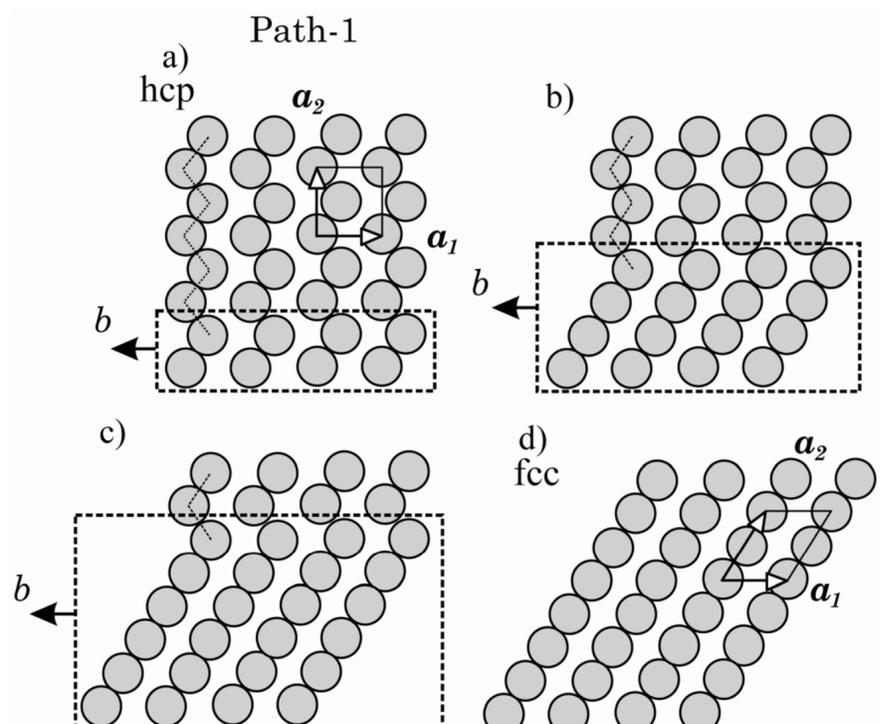


Energy barrier from hcp to dhcp (at experimental  $c/a$ ) is  $\Delta E = 16.8$  meV/atom (GGA) or 12.2 meV/atom (LDA), respectively. An estimate of the transformation temperature by  $T = \Delta E / k_B$  yields  $T = 195$  K (or 142 K).

**This transformation is experimentally observed**

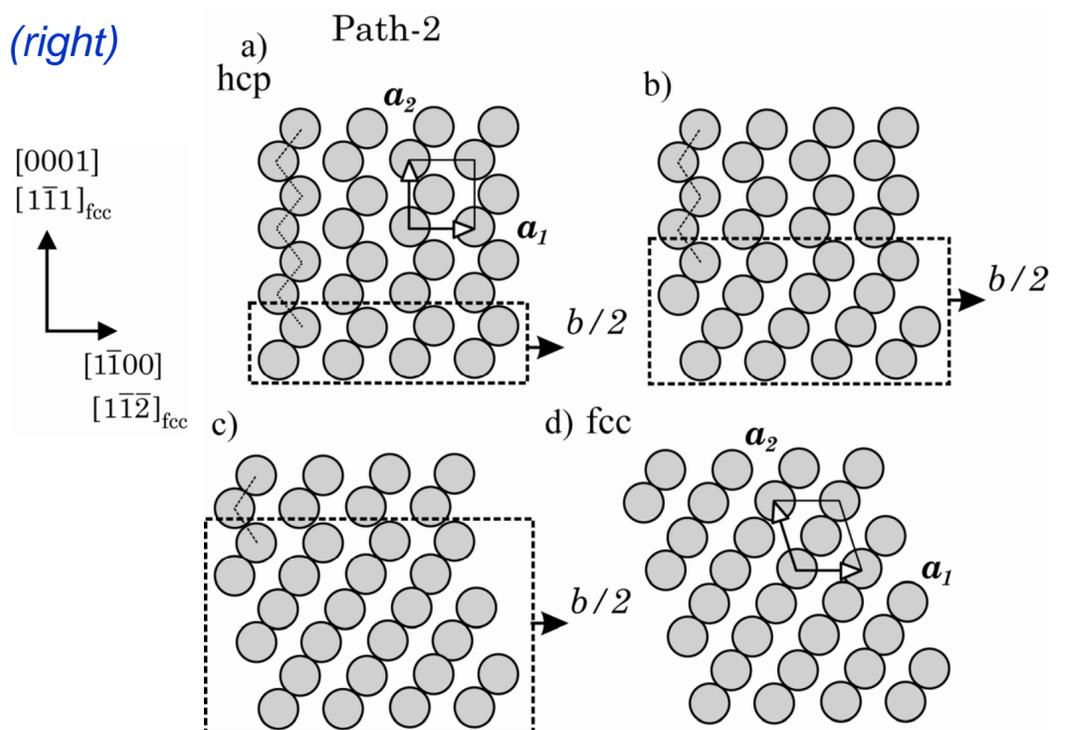
### Three proposed hcp $\rightarrow$ fcc paths: Path-1 (right)

The hexagonal (0001) double layers are shifted by the distance of  $b = 2d_{NN}\sqrt{3}/3$  in the  $[\bar{1}100]$  direction.

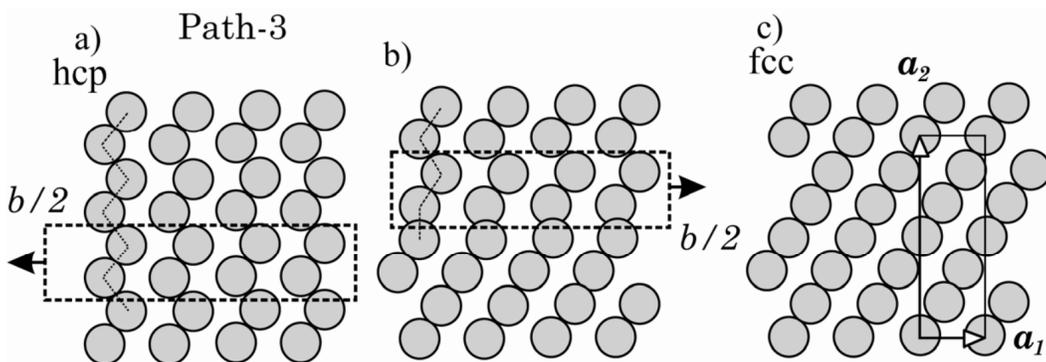


### Proposed hcp → fcc paths: Path-2 (right)

The hexagonal (0001) double layers are shifted by the distance of  $b/2 = d_{NN} \sqrt{3}/3$  in the  $[1\bar{1}00]$  direction.

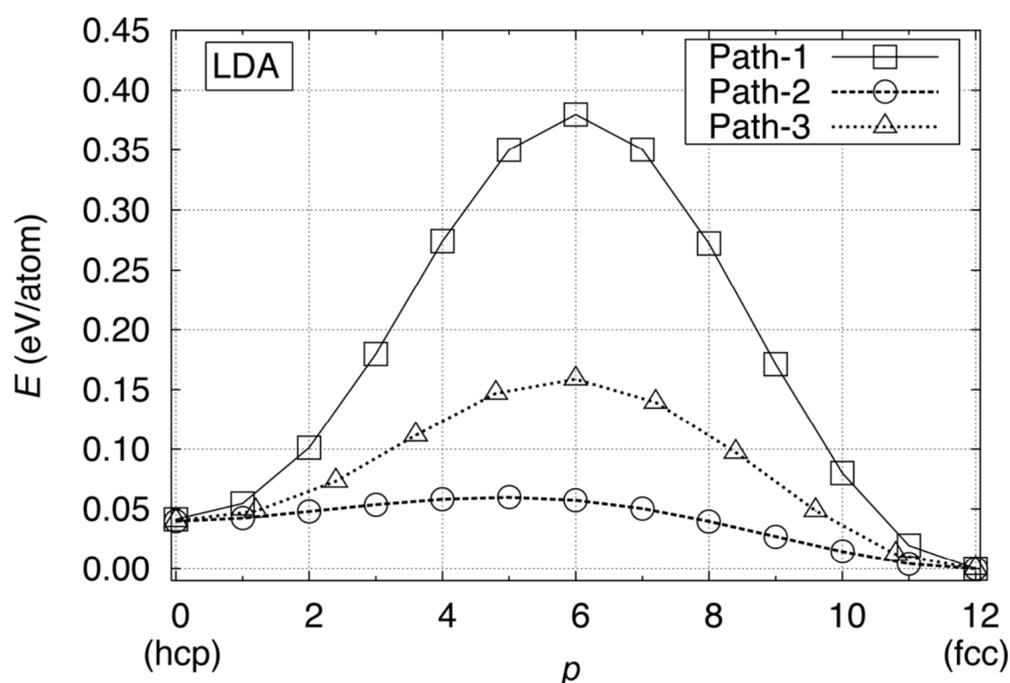


### Proposed hcp → fcc paths: Path-3 (bottom)



The hexagonal (0001) double layers are shifted by the distance of  $b/2 = d_{NN} \sqrt{3}/3$  in two opposite directions  $[\bar{1}100]$  and  $[1\bar{1}00]$

### Total energy profiles of the hcp → fcc paths (LDA)



The energy barrier of Path-2 from hcp to fcc structure amounts to 25 meV/atom ( $T = 290$  K, GGA) or 20 meV/atom ( $T = 232$  K, LDA), respectively.

### Discussion of the energy profiles

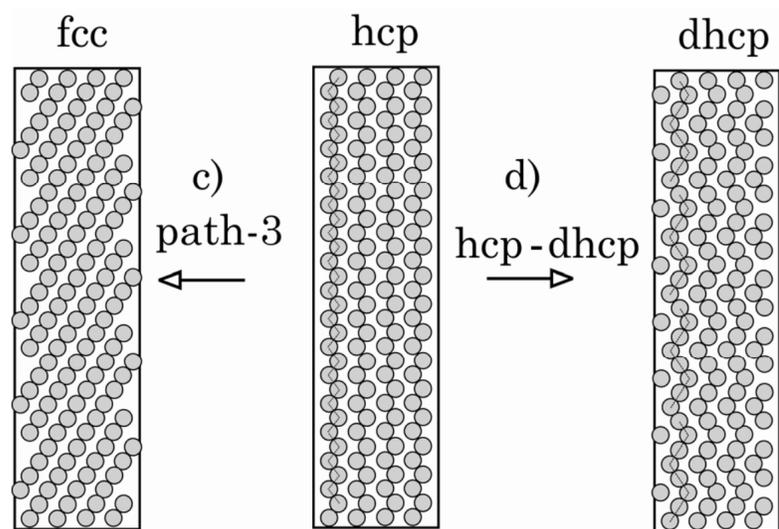
The height of the energy barrier at hcp → fcc path-2 ( $\sim 260$  K) is comparable to the energy barrier of the hcp → dhcp path ( $\sim 170$  K), but unlike the hcp → dhcp path, **the transformation via hcp → fcc path-2 was not observed to operate** in Pd films on cubic substrates, even for thick films (more than 100 monolayers and more).

What are the **stabilizing agents** for the hcp Pd structure present in the thin films on cubic substrates?

- (i) the need to overcome epitaxial stresses caused by the misfit of the adsorbate and substrate
- (ii) the domain topology of the Pd films (they grow in orthogonal set of rectangular domains)

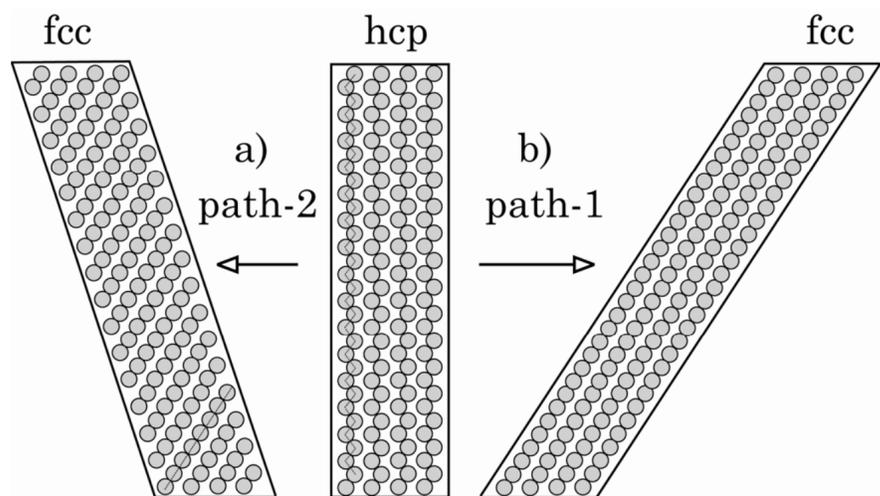
## hcp-fcc path-3 and hcp-dhcp path — no change in shape of the domains

The transformation from hcp to fcc via hcp  $\rightarrow$  fcc path-3 and the proposed hcp  $\rightarrow$  dhcp path do not require change of the rectangular domains of hcp Pd structure in the Pd film. However, hcp  $\rightarrow$  fcc path-3 requires a very high transition temperature of 1470 K (hcp  $\rightarrow$  dhcp requires about 170 K)



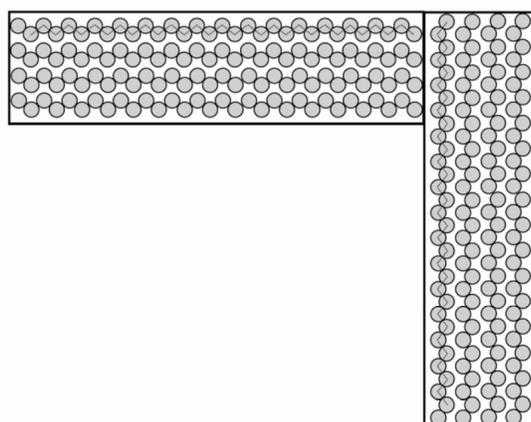
## hcp-fcc paths 1 and 2 — change of shape of the domains is needed

The transformations hcp  $\rightarrow$  fcc via path-1 or path-2 require a change of shape of every individual (initially rectangular) domain of hcp Pd regions. Although a “free” hcp  $\rightarrow$  fcc path-2 would require a transition temperature of only  $\sim 260$  K, the transformation is blocked by the necessity of long-distance movement of atoms.

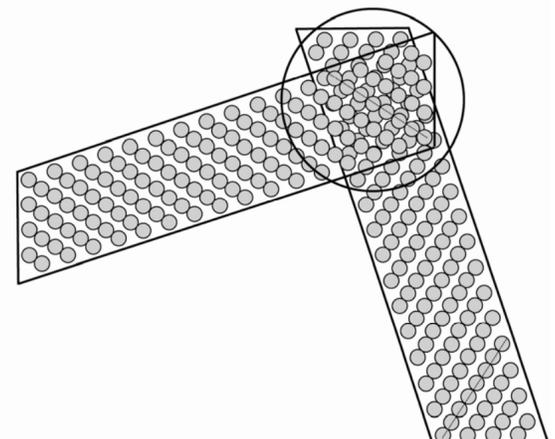


The hcp  $\rightarrow$  fcc transformation via path-2 would break the orthogonal domain arrangement (right)

a) two orthogonal hcp Pd domains



b) these domains after Path-2



## Conclusions

*Ab initio* calculations allow us to understand the stability of hcp Pd structure in thin films on cubic substrates [W(001), also Nb(001)]. Unlike the hcp  $\rightarrow$  dhcp transformation, the studied hcp  $\rightarrow$  fcc transformations are not observed experimentally because:

- (i) transformations via hcp  $\rightarrow$  fcc path-1 and path-3 exhibit too high energy barriers (4160 K, 1470 K)
- (ii) transformation via hcp  $\rightarrow$  fcc path-2 exhibits a low energy barrier ( $\sim 260$  K), but it is blocked by the arrangement of mutually orthogonal rectangular domains of hcp Pd.  $\Rightarrow$

*The domain topology acts as an external agent stabilizing the hcp Pd structure in films on cubic substrates.*

## References

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